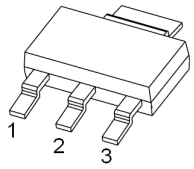
JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

SOT-223 Plastic-Encapsulate Transistors

SOT-223



1. BASE
2. COLLECTOR
3. EMITTER

PZTA56 TRANSISTOR (PNP)

FEATURES

- Low Voltage and High Current
- General Purpose Amplifier Applications

MAXIMUM RATINGS (T_a=25℃ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-80	V
V_{CEO}	Collector-Emitter Voltage	-80	V
V_{EBO}	Emitter-Base Voltage	-4	V
I_C	Collector Current	-500	mA
P_C	Collector Power Dissipation	1	W
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	125	℃/W
T_j	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-55~+150	℃

ELECTRICAL CHARACTERISTICS (T_a=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=-0.1mA,I_E=0	-80			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$*	I_C=-1mA,I_B=0	-80			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=-0.1mA,I_C=0	-4			V
Collector cut-off current	I_{CBO}	V_{CB}=-80V,I_E=0			-100	nA
Collector cut-off current	I_{CEO}	V_{CE}=-60V,I_B=0			-100	nA
Emitter cut-off current	I_{EBO}	V_{EB}=-3V, I_C=0			-100	nA
DC current gain	$h_{FE(1)}$	V_{CE}=-1V, I_C=-10mA	100			
	$h_{FE(2)}$	V_{CE}=-1V, I_C=-100mA	100			
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-100mA,I_B=-10mA			-0.25	V
Base-emitter voltage	V_{BE}	V_{CE}=-1V, I_C=-100mA			-1.2	V
Transition frequency	f_T	V_{CE}=-1V,I_C=-100mA, f=100MHz	50			MHz

*Pulse test: pulse width ≤300μs, duty cycle≤ 2.0%.